



APPLICANT'S ART CITATION (Use several sheets if necessary)	Application <b>09/658,732</b>	OFGS File No. <b>P/1071-1118</b>
	Applicant <b>Makoto INAI, et al.</b>	
	Filing Date <b>September 11, 2000</b>	Group Art Unit <b>----</b>

## U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Sub-class	Filing Date If Appropriate

## FOREIGN PATENT DOCUMENTS

Document Number	Date	Country	Class	Sub-class	Translation	
					Yes	No

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<b>BMB</b>	Makoto INAI, et al. "Doped Channel HFET with Effective Lateral Energy Modulation for High Power Enhancement Operation", Extended Abstracts of the 1998 International Conference on Solid State Devices and Materials, Hiroshima, 1998, pages 328-329.

Examiner <b>BMB</b>	Date Considered <b>11/20/01</b>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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